

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

IAP9 Rec'd PCT/PTO 13 DEC 2005

Masahiro SAKURADA et al.

Application No.: New National Stage Patent Application of PCT/JP2004/007350

Filed: December 13, 2005

Docket No.: 126274

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL AND A SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

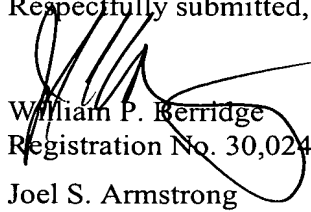
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the non-English language Reference 7 is discussed in the present specification.
- ☒ 3. References were 1-6 cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. Copies of the references are attached hereto.
- ☒ 4. English language Abstracts of the non-English language References 1-7 are attached hereto.
- ☒ 5. Computer-generated English language translations of the following Japanese Patent Publications have been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and are attached, but have not been reviewed for accuracy. See References 1-7.

Respectfully submitted,


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DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126274		APPLICATION NO. New National Stage Patent Application of PCT/JP2004/007350	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Masahiro SAKURADA et al.			
				FILING DATE December 13, 2005			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
	1	JP A 2003-002786 w/abst. & trans	01/08/2003	JAPAN			
	2	JP A 08-268794 w/abst. & trans	10/15/1996	JAPAN			
	3	JP A 08-330316 w/abst. & trans	12/13/1996	JAPAN			
	4	JP A 2000-063196 w/abst. & trans	02/29/2000	JAPAN			
	5	JP A 2000-313691 w/abst. & trans	11/14/2000	JAPAN			
	6	JP A 2002-338389 w/abst. & trans	11/27/2002	JAPAN			
	7	JP A 11-147786 w/abst. & trans	06/02/1999	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	8	V. V. Voronkov, " The mechanism of Swirl Defects formation in Silicon," Journal of Crystal Growth, 59 (1982), 625-643.					
	9	F. Dupret et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No 9, pp. 1849-1871, 1990.					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 13, 2005